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# Syntheses and Crystal Structure of the Ternary Silicides $RE_2Si_2Mg$ (RE = Y, La–Nd, Sm, Gd–Lu) and Structure Refinement of Dy<sub>5</sub>Si<sub>3</sub>

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**Summary.** The rare earth metal-magnesium-silicides  $RE_2Si_2Mg$  (RE = Y, La-Nd, Sm, Gd-Lu) were prepared by induction melting of the elements in sealed tantalum tubes in a water-cooled sample chamber of a high-frequency furnace. The silicides were investigated *via* X-ray powder diffraction. The structures of Sm<sub>2</sub>Si<sub>2</sub>Mg and Dy<sub>2</sub>Si<sub>2</sub>Mg were refined from X-ray single crystal diffractometer data: Mo<sub>2</sub>FeB<sub>2</sub> type, P4/mbm, a = 727.86(7), c = 428.16(6) pm, wR2 = 0.0194, 206  $F^2$  values, 13 variable parameters for Sm<sub>2</sub>Si<sub>2</sub>Mg and a = 713.85(7), c = 419.07(6) pm, wR2 = 0.0331, 286  $F^2$  values, 12 variable parameters for Dy<sub>2</sub>Si<sub>2</sub>Mg. The samarium compound shows a small homogeneity range Sm<sub>2+x</sub>Si<sub>2</sub>Mg<sub>1-x</sub>. The investigated single crystal had the refined composition Sm<sub>2.022(3</sub>Si<sub>2</sub>Mg<sub>0.978(3)</sub>. The  $RE_2$ Si<sub>2</sub>Mg silicides are 1:1 intergrowth structures of CsCl and AlB<sub>2</sub> related slabs of compositions REMg and  $RESi_2$ . Crystals of the binary silicide Dy<sub>5</sub>Si<sub>3</sub> were obtained as side product. The structure was refined from X-ray single crystal data: Mn<sub>5</sub>Si<sub>3</sub> type,  $P6_3/mcm$ , a = 841.0(2), c = 631.3(1) pm, wR2 = 0.0661, 269  $F^2$  values, 12 variable parameters.

Keywords. Rare Earth Compounds; Silicides; Crystal Chemistry.

## Introduction

The binary transition metal (*T*), rare earth metal (*RE*), and actinoid (*An*) silicides  $T_3Si_2$  (T = Cr, Zr, Nb, Mo, Hf, W),  $RE_3Si_2$  (RE = La, Ce, Pr), and  $An_3Si_2$  (An = Th, U, Np, Pu) with tetragonal U<sub>3</sub>Si<sub>2</sub> type are 1:1 intergrowth structures of distorted AlB<sub>2</sub>- and W-like slabs of compositions  $TSi_2$  ( $RESi_2$ ,  $AnSi_2$ ) and  $T_2$  ( $RE_2$ ,  $An_2$ ). An overview on these compounds is given in a recent review [1]. The W-like slabs can also be occupied by two different metals in an ordered manner, leading to CsCl related slabs. With this ordering pattern, the ternary silicides  $RE_2Si_2Al$ 

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(RE = Sc, Yb) [2, 3],  $RE_2Si_2Li$  (RE = Y, Nd) [4],  $Ce_2Si_2Mg$  [5],  $Dy_2Al_2Si$  [6],  $RE_2Si_2Sc$  (RE = Ce, Nd, Sm) [7–10], and  $RE_2Si_2Y$  (RE = La, Ce) [8] have been reported. In the germanium based systems, only the series of  $RE_2Ge_2Mg$  (RE = Y, La–Nd, Sm, Gd, Tb) germanides [11, 12] is known.

We have now started a more systematic investigation of the silicon based ternary systems with respect to  $U_3Si_2$  type compounds. Herein we report on the synthesis and structural characterization of the ternary silicides  $RE_2Si_2Mg$  with RE = Y, La–Nd, Sm, Gd–Lu. So far, only lattice parameters of the 12 K antiferromagnet Ce<sub>2</sub>Si<sub>2</sub>Mg [5] have been reported. The existence of La<sub>2</sub>Si<sub>2</sub>Mg, Ce<sub>2</sub>Si<sub>2</sub>Mg, Nd<sub>2</sub>Si<sub>2</sub>Mg [13], and Yb<sub>2</sub>Si<sub>2</sub>Mg [14] has been announced, however, to the best of our knowledge, no basic crystallographic parameters have been reported.

During our phase analytical investigations we got also single crystals of the binary silicide  $Dy_5Si_3$  with  $Mn_5Si_3$  type structure. Up to now, only powder data are available for this 125 K antiferromagnet [15–19]. A single crystal structure refinement is reported herein.

### **Results and Discussion**

The ternary silicides  $RE_2Si_2Mg$  (RE = Y, La–Nd, Sm, Gd–Lu) have been prepared and characterized by X-ray diffraction. They crystallize with a ternary ordered version of the U<sub>3</sub>Si<sub>2</sub> type [1] and are isotypic with the recently reported germanides  $RE_2Ge_2Mg$  (RE = Y, La–Nd, Sm, Gd, Tb) [12]. The cell volumes are plotted in Fig. 1 as a function of the rare earth element. As expected from the lanthanoid contraction, the cell volume decreases from the lanthanum to the lutetium compound. Similar to the germanide series, also the Y<sub>2</sub>Si<sub>2</sub>Mg cell volume fits between the terbium and the dysprosium compound. The volumes of the silicides are between 2–3% smaller than those of the germanides. The cerium and ytterbium compounds show no anomaly in the cell volume. We can thus expect stable trivalent cerium and ytterbium in Ce<sub>2</sub>Si<sub>2</sub>Mg and Yb<sub>2</sub>Si<sub>2</sub>Mg. For Ce<sub>2</sub>Si<sub>2</sub>Mg, the trivalent state was evident from the magnetic data (2.47  $\mu_B$ /Ce atom) [5].

As is evident from Fig. 2, the  $RE_2Si_2Mg$  silicides are intergrowth structures of distorted CsCl and AlB<sub>2</sub> related slabs of compositions *REMg* and *RESi*<sub>2</sub>. The Si–Si



**Fig. 1.** Plot of the cell volumes of the  $RE_2Si_2Mg$  silicides



**Fig. 2.** Projection of the Dy<sub>2</sub>Si<sub>2</sub>Mg structure onto the *xy* plane; all atoms lie on mirror planes at z=0 (Si, Mg) and z=1/2 (Dy); dysprosium, silicon, and magnesium atoms are drawn as grey, filled, and open circles, respectively; the CsCl and AlB<sub>2</sub> related slabs and the [Si<sub>2</sub>Mg] network are emphasized

distances of 239 pm in  $\text{Sm}_2\text{Si}_2\text{Mg}$  and  $\text{Dy}_2\text{Si}_2\text{Mg}$  are close to the Si–Si single bond distance of 235 pm in elemental silicon [25]. The crystal chemistry of  $\text{Mo}_2\text{FeB}_2$ type intermetallics has recently been reviewed [1]. For more details we refer to this article. Chemical bonding in the  $RE_2\text{Si}_2\text{Mg}$  intermetallics can safely be described within a rigid band model in comparison with  $\text{Ce}_2\text{Ge}_2\text{In}$  [26] and  $\text{Gd}_2\text{Ge}_2\text{Mg}$  [11]. The electronic structure calculations for these germanides revealed strong Ge–Ge bonding within the Ge<sub>2</sub> dumb-bells.

Atom	<i>Wyckoff</i> site	x	у	Z	$U_{ m eq}$
Sm <sub>2.022(3)</sub> Si <sub>2</sub> N	/Ig <sub>0.978(3)</sub>				
Sm	4h	0.17888(2)	1/2 + x	1/2	63(1)
Si	4g	0.3837(1)	1/2 + x	0	72(3)
Mg/Sm <sup>a</sup>	2a	0	0	0	104(8)
Dy <sub>2</sub> Si <sub>2</sub> Mg					
Dy	4h	0.17820(2)	1/2 + x	1/2	56(1)
Si	4g	0.3816(2)	1/2 + x	0	54(3)
Mg	2a	0	0	0	80(5)
Dy <sub>5</sub> Si <sub>3</sub>					
Dy1	6 <i>g</i>	0.24375(10)	0	1/4	93(3)
		0.2370(3)			
Dy2	4d	2/3	1/3	0	106(3)
Si	6 <i>g</i>	0.6066(6) 0.6143(4)	0	1/4	95(9)

**Table 1.** Atomic coordinates and isotropic displacement parameters (pm<sup>2</sup>) for Sm<sub>2.022(3)</sub>Si<sub>2</sub>Mg<sub>0.978(3)</sub>, Dy<sub>2</sub>Si<sub>2</sub>Mg (space group P4/mbm), and Dy<sub>5</sub>Si<sub>3</sub> (space group  $P6_3/mcm$ );  $U_{eq}$  is defined as a third of the trace of the orthogonalized  $U_{ij}$  tensor; the positional parameters of Dy<sub>5</sub>Si<sub>3</sub> derived from neutron powder data [19] are given in italics

<sup>a</sup> This site shows mixed occupancy: 97.8(3)% Mg and 2.2(3)% Sm

Single crystals of  $Dy_5Si_3$  were obtained as a side product during the first synthesis attempts for  $Dy_2Si_2Mg$ . So far, this binary silicide was only characterized on the basis of X-ray and neutron powder data [15–19]. The single crystal data essentially confirm the structure refinement at 150 K based on neutron powder data [19], however, the positional parameters determined here from the single crystal X-ray data are slightly different (Table 1). This has a drastic effect especially of the Dy–Si interatomic distances which differ by up to 10 pm (Table 1). The difference in the positional parameters and thus the interatomic distances is most likely due to the different data collection temperatures (RT *vs.* 150 K). The crystal chemistry and chemical bonding of isotypic Lu<sub>5</sub>Si<sub>3</sub> [24] has been discussed recently. For details and drawings we refer to this paper.

## **Experimental**

#### Synthesis

Starting materials for the preparation of the silicides  $RE_2Si_2Mg$  and  $Dy_5Si_3$  were ingots of the rare earth metals (Johnson Matthey, Chempur, or Kelpin, >99.9%), silicon lumps (Wacker, >99.9%), and a magnesium rod (Johnson Matthey,  $\emptyset$  16 mm, >99.5%). In a first step, the rare earth metal pieces were melted under 600 mbar argon to small buttons in an arc-melting furnace [20]. The argon was purified over titanium sponge (900 K), silica gel, and molecular sieves. The surface of the magnesium rod was then removed on a turning lathe in order to remove impurities and the rod was subsequently cut into thin plates. Pieces of the magnesium rod, the arc-melted rare earth metal buttons, and pieces of the silicon lumps were then weighed in the ideal 2*RE*:2Si:1Mg atomic ratios and sealed in small tantalum tubes (*ca.* 1 cm<sup>3</sup> volume) under an argon pressure of *ca.* 800 mbar.

The tantalum containers were put in a water-cooled sample chamber [21] of a high-frequency furnace (Hüttinger Elektronik, Freiburg, Typ TIG 5/300), heated for 15 minutes at *ca*. 1500 K and subsequently annealed for another 4 hours at ca. 1070 K. Finally the tube was quenched to room temperature by switching off the power of the generator. The temperature was controlled through a Sensor Therm Metis MS09 pyrometer with an accuracy of  $\pm 30$  K.

The brittle products could easily be separated from the tantalum tubes. No reaction with the container material was observed. In some cases, small irregularly shaped single crystals with metallic lustre occurred directly after the inductive annealing process. During several preparations small amounts of volatile magnesium had distilled at the upper, colder parts of the tantalum tubes, leading to a lower magnesium content in the sample. This way the binary silicide Dy<sub>5</sub>Si<sub>3</sub> formed. Compact pieces and powders of the silicides are stable in air over months.

#### Scanning Electron Microscopy

The single crystals investigated on the diffractometer have been analyzed by EDX measurements using a LEICA 420 I scanning electron microscope with the rare earth trifluorides, SiO<sub>2</sub>, and MgO as standards. No impurity elements were detected. Various point analyses on the crystals revealed the compositions  $45 \pm 2$  at.-% Sm: $39 \pm 2$  at.-% Si: $16 \pm 2$  at.-% Mg,  $38 \pm 2$  at.-% Dy: $40 \pm 2$  at.-% Si: $22 \pm 2$  at.-% Mg, and  $55 \pm 3$  at.-% Dy: $45 \pm 3$  at.-% Si, close to the values obtained from the structure refinements. The EDX analyses nicely reflect the slightly higher samarium content observed for Sm<sub>2.022(3)</sub>Si<sub>2</sub>Mg<sub>0.978(3)</sub>.

#### X-Ray Film Data and Structure Refinemens

All samples were studied through *Guinier* powder patterns using Cu  $K\alpha_1$  radiation and  $\alpha$ -quartz (a = 491.30, c = 540.46 pm) as an internal standard. The *Guinier* camera was equipped with an imaging plate system (Fujifilm BAS-1800). The lattice parameters (Table 2) were deduced from

The Silicides *RE*<sub>2</sub>Si<sub>2</sub>Mg and Dy<sub>5</sub>Si<sub>3</sub>

Compound	$a/{ m pm}$	$c/{ m pm}$	V/nm <sup>3</sup>
Y <sub>2</sub> Si <sub>2</sub> Mg	714.35(5)	420.72(2)	0.2147
La <sub>2</sub> Si <sub>2</sub> Mg	752.25(8)	446.26(6)	0.2525
Ce <sub>2</sub> Si <sub>2</sub> Mg	742.4(1)	438.90(9)	0.2419
$Ce_2Si_2Mg$ [2]	743.0	439.1	0.2424
Pr <sub>2</sub> Si <sub>2</sub> Mg	740.09(6)	436.02(6)	0.2388
Nd <sub>2</sub> Si <sub>2</sub> Mg	734.62(7)	433.84(5)	0.2341
Sm <sub>2</sub> Si <sub>2</sub> Mg	727.86(7)	428.16(6)	0.2268
Gd <sub>2</sub> Si <sub>2</sub> Mg	720.33(9)	425.10(8)	0.2206
Tb <sub>2</sub> Si <sub>2</sub> Mg	716.51(9)	420.82(8)	0.2160
Dy <sub>2</sub> Si <sub>2</sub> Mg	713.85(7)	419.07(6)	0.2136
Ho <sub>2</sub> Si <sub>2</sub> Mg	711.27(8)	417.28(6)	0.2111
Er <sub>2</sub> Si <sub>2</sub> Mg	708.92(7)	416.12(6)	0.2091
Tm <sub>2</sub> Si <sub>2</sub> Mg	708.3(1)	413.33(7)	0.2074
Yb <sub>2</sub> Si <sub>2</sub> Mg	704.9(1)	412.24(8)	0.2048
$Lu_2Si_2Mg$	702.1(1)	411.41(9)	0.2028
Dy <sub>5</sub> Si <sub>3</sub>	841.0(2)	631.3(1)	0.3867
Dy <sub>5</sub> Si <sub>3</sub> [16]	839	628	0.3828
Dy <sub>5</sub> Si <sub>3</sub> [17]	837.9(3)	629.0(2)	0.3825
Dy <sub>5</sub> Si <sub>3</sub> [19] (150 K data)	836.89(5)	629.60(4)	0.3819

**Table 2.** Lattice parameters of the tetragonal silicides  $RE_2Si_2Mg$  (space group P4/mbm, Mo<sub>2</sub>FeB<sub>2</sub> type) and Dy<sub>5</sub>Si<sub>3</sub> (space group  $P6_3/mcm$ , Mn<sub>5</sub>Si<sub>3</sub> type)

least-squares fits of the powder data. The indexing of the powder patterns was facilitated through intensity calculations [22] using the atomic positions obtained from the structure refinements. The lattice parameters derived here for  $Ce_2Si_2Mg$  and  $Dy_5Si_3$  are in good agreement with the literature data (see Table 2).

Small, irregularly shaped single crystals of Sm<sub>2</sub>Si<sub>2</sub>Mg, Dy<sub>2</sub>Si<sub>2</sub>Mg, and Dy<sub>5</sub>Si<sub>3</sub> were selected from the annealed samples and examined by *Laue* photographs on a *Buerger* precession camera (equipped with an imaging plate system Fujifilm BAS-1800) in order to establish suitability for intensity data collection. Intensity data were recorded at room temperature by use of a four-circle diffractometer (CAD4) with graphite monochromatized MoK<sub> $\alpha$ </sub> radiation ( $\lambda = 71.073$  pm) and a scintillation counter with pulse-height discrimination. The scans were taken in the  $\omega/2\theta$  mode and empirical absorption corrections were applied on the basis of psi-scan data followed by spherical absorption corrections. All relevant crystallographic details for the data collections and evaluations are listed in Table 3.

The isotypy of the  $RE_2Si_2Mg$  silicides with the recently reported germanides was already evident from the *Guinier* data. The atomic positions of Ce<sub>2</sub>Ge<sub>2</sub>Mg [12] were taken as starting values and the structures of Sm<sub>2</sub>Si<sub>2</sub>Mg and Dy<sub>2</sub>Si<sub>2</sub>Mg were successfully refined using SHELXL-97 (full-matrix leastsquares on  $F_0^2$ ) [23] with anisotropic atomic displacement parameters for all sites.

Since the isotypic germanide  $La_{2+x}Ge_2Mg_{1-x}$  showed a significant homogeneity range, the occupancy parameters of  $Sm_2Si_2Mg$  and  $Dy_2Si_2Mg$  were refined in separate series of least-squares cycles. While all sites of  $Dy_2Si_2Mg$  were fully occupied within one standard deviation, a small homogeneity range was observed for the samarium based crystal, leading to the composition  $Sm_{2.022(3)}Si_2Mg_{0.978(3)}$  for the investigated crystal.

The atomic positions of  $Lu_5Si_3$  [24] were taken as starting values for  $Dy_5Si_3$ . The refinement went smoothly to the residuals listed in Table 3. All sites were fully occupied within two standard deviations. Final difference *Fourier* synthesis revealed no significant residual peaks for all three data sets (see Table 3). The positional parameters and interatomic distances are listed in Tables 1 and 4. Further

Empirical formula	Sm <sub>2.022(3)</sub> Si <sub>2</sub> Mg <sub>0.978(3)</sub>	Dy <sub>2</sub> Si <sub>2</sub> Mg	Dy <sub>5</sub> Si <sub>3</sub>
Molar mass	381.19 g/mol	405.49 g/mol	896.77 g/mol
Unit cell dimensions	Table 1	Table 1	Table 1
Calculated density	$5.58  {\rm g/cm^3}$	$6.31  {\rm g/cm^3}$	$7.70 \mathrm{g/cm^{3}}$
Crystal size	$20 \times 30 \times 30 \mu \mathrm{m}^3$	$15 \times 40 \times 60 \mu \text{m}^3$	$40 \times 60 \times 60 \mu \text{m}^3$
Transm. Ratio (max/min)	0.641/0.480	0.652/0.473	0.714/0.409
Absorption coefficient	$26.1 \text{ mm}^{-1}$	$35.2  \text{mm}^{-1}$	$48.1  \text{mm}^{-1}$
<i>F</i> (000)	328	344	744
$\theta$ range	$3^{\circ}$ to $30^{\circ}$	$4^{\circ}$ to $35^{\circ}$	$3^{\circ}$ to $35^{\circ}$
Range in hkl	$\pm 10, \pm 10, \pm 6$	$\pm 11, \pm 11, \pm 6$	$\pm 13, \pm 13, +8$
Total no. reflections	2436	3339	2654
Independent reflections	206 ( $R_{\rm int} = 0.0399$ )	286 ( $R_{\rm int} = 0.0606$ )	269 ( $R_{\text{int}} = 0.1212$ )
Reflections with $I > 2\sigma(I)$	192	264	204
	$(R_{\rm sigma} = 0.0155)$	$(R_{\rm sigma} = 0.0217)$	$(R_{\rm sigma} = 0.0424)$
Data/parameters	206/13	286/12	269/12
Goodness-of-fit on $F^2$	1.254	1.130	1.060
Final <i>R</i> indices $[I > 2\sigma(I)]$	R1 = 0.0121	R1 = 0.0162	R1 = 0.0311
	wR2 = 0.0192	wR2 = 0.0324	wR2 = 0.0603
R indices (all data)	R1 = 0.0142	R1 = 0.0192	R1 = 0.0515
	wR2 = 0.0194	wR2 = 0.0331	wR2 = 0.0661
Extinction coefficient	0.0153(6)	0.0148(9)	0.0113(9)
Largest diff. Peak	0.61 and	1.12 and	3.06 and
and hole	$-0.69 \mathrm{e}/\mathrm{\AA}^3$	$-1.30  e/Å^3$	$-1.66 \mathrm{e}/\mathrm{\AA}^3$

**Table 3.** Crystal data and structure refinement for  $Sm_{2.022(3)}Si_2Mg_{0.978(3)}$ ,  $Dy_2Si_2Mg$  (space group P4/mbm, Z = 2), and  $Dy_5Si_3$  (space group  $P6_3/mcm$ , Z = 2)

**Table 4.** Interatomic distances (pm) in the structures of  $Sm_{2.022}Si_2Mg_{0.978}$ ,  $Dy_2Si_2Mg$ , and  $Dy_5Si_3$  calculated with the lattice parameters taken from X-ray powder data; standard deviations are given in parenthesis; the 150 K neutron powder data from Ref. [19] are listed for comparison

Sm <sub>2.022</sub> Si <sub>2</sub> Mg <sub>0.978</sub>		Dy <sub>2</sub> S	Dy <sub>2</sub> Si <sub>2</sub> Mg		Dy <sub>5</sub> Si	Dy <sub>5</sub> Si <sub>3</sub> (this work)			Dy <sub>5</sub> Si <sub>3</sub> [19]			
Sm:	2	Si	300.5(1)	Dy:	2	Si	293.4(1)	Dy1:	2	Si	289.3(4)	282.0
	4	Si	306.7(1)	•	4	Si	300.9(1)	•	1	Si	305.1(5)	315.8
	4	Mg	342.7(1)		4	Mg	335.9(1)		2	Si	339.8(2)	338.5
	1	Sm	368.3(1)		1	Dy	359.8(1)		2	Dy1	355.1(2)	343.5
	4	Sm	378.4(1)		4	Dy	371.4(1)		4	Dy2	361.0(1)	362.7
	2	Sm	428.2(1)		2	Dy	419.1(1)		4	Dy1	376.4(1)	372.1
Si:	1	Si	239.4(3)	Si:	1	Si	239.0(3)	Dy2:	6	Si	303.1(2)	303.8
	2	Mg	291.8(1)		2	Mg	285.2(1)		2	Dy2	315.7(1)	314.8
	2	Sm	300.5(1)		2	Dy	293.4(1)		6	Dy1	361.0(1)	362.7
	4	Sm	306.7(1)		4	Dy	300.9(1)	Si:	2	Dy1	289.3(4)	282.0
Mg:	4	Si	291.8(1)	Mg:	4	Si	285.2(1)		4	Dy2	303.1(2)	303.8
	8	Sm	342.7(1)	-	8	Sm	335.9(1)		1	Dy1	305.1(5)	315.8
_									2	Dy1	339.8(2)	338.5

details on the structure refinements may be obtained from Fachinformationszentrum Karlsruhe, D-76344 Eggenstein-Leopoldshafen (Germany), by quoting the Registry Nos. CSD-415116 ( $Sm_{2.022}Si_2Mg_{0.978}$ ), CSD-415117 ( $Dy_2Si_2Mg$ ), and CSD-415118 ( $Dy_5Si_3$ ).

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